V_{RSM}	=	5200 V
I_{FAVM}	=	1028 A
I_{FRMS}	=	1614 A
I_{FSM}	=	12.8×10^3 A
V_{F0}	=	0.894 V
r_F	=	0.487 mΩ

Rectifier Diode
5SDD 08D5000

Doc. No. 5SYA1165-00 Jan. 03

- **Very low on-state losses**
- **Optimum power handling capability**

Blocking

Maximum rated values [1)]

Parameter	Symbol	Conditions	Value	Unit
Repetetive peak reverse voltage	V_{RRM}	f = 50 Hz, t_p = 10ms, T_j = -40...160°C	5000	V
Non - repetetive peak reverse voltage	V_{RSM}	f = 5 Hz, t_p = 10ms, T_j = -40...160°C	5200	V

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. (reverse) leakage current	I_{RRM}	V_{RRM}, Tj = 160°C			30	mA

Mechanical data

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	F_M		8	10	12	kN
Acceleration	a	Device unclamped			50	m/s^2
Acceleration	a	Device clamped			100	m/s^2

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Weight	m			0.3		kg
Housing thickness	H			26		mm
Pole-piece diameter	D_P			34		mm
Surface creepage distance	D_S		30			mm
Air strike distance	D_a		18			mm

1) Maximum rated values indicate limits beyond which damage to the device may occur

On-state

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Max. average on-state current	I_{FAVM}	50 Hz, Half sine wave, T_C = 85 °C			1028	A
Max. RMS on-state current	I_{FRMS}				1614	A
Max. peak non-repetitive surge current	I_{FSM}	t_p = 10 ms, T_j = 160°C, V_R = 0 V			12.8×10^3	A
Limiting load integral	I^2t				682×10^3	A^2s
Max. peak non-repetitive surge current	I_{FSM}	t_p = 8.3 ms, T_j = 160°C, V_R = 0 V			12×10^3	A
Limiting load integral	I^2t				720×10^3	A^2s

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	V_F	I_F = 1500 A, T_j = 160°C			1.65	V
Threshold voltage	$V_{(T0)}$	T_j = 160°C I_T = 1500...4500 A			0.894	V
Slope resistance	r_T				0.487	mΩ

Switching

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Recovery charge	Q_{rr}	di_F/dt = -30 A/µs, V_R = 100 V I_{FRM} = 1000 A, T_j = 160°C		2400	3500	µAs

Thermal

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	typ	max	Unit
Operating junction temperature range	T_{vj}		-40		160	°C
Storage temperature range	T_{stg}		-40		160	°C

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction to case	$R_{th(j-c)}$	Double-side cooled			32	K/kW
	$R_{th(j-c)A}$	Anode-side cooled			50	K/kW
	$R_{th(j-c)C}$	Cathode-side cooled			88	K/kW
Thermal resistance case to heatsink	$R_{th(c-h)}$	Double-side cooled			8	K/kW
	$R_{th(c-h)}$	Single-side cooled			16	K/kW

Analytical function for transient thermal impedance:

$$Z_{thJC}(t) = \sum_{i=1}^{n} R_i\left(1 - e^{-t/\tau_i}\right)$$

i	1	2	3	4
R_i(K/kW)	11.600	10.110	7.870	2.410
τ_i(s)	0.7033	0.2185	0.0588	0.0042

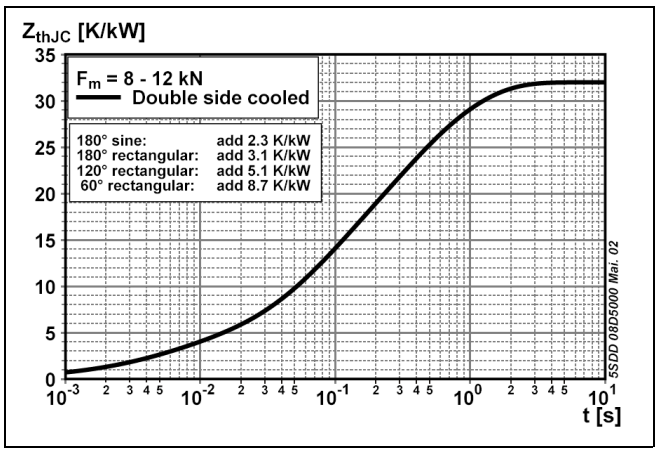

Fig. 1 Transient thermal impedance junction-to-case.

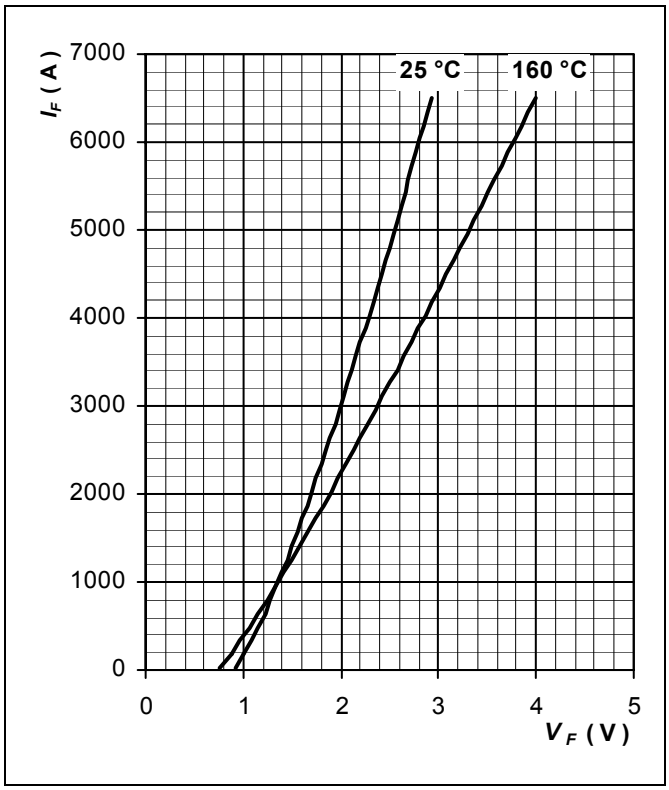

Fig. 2 Max. on-state characteristics.

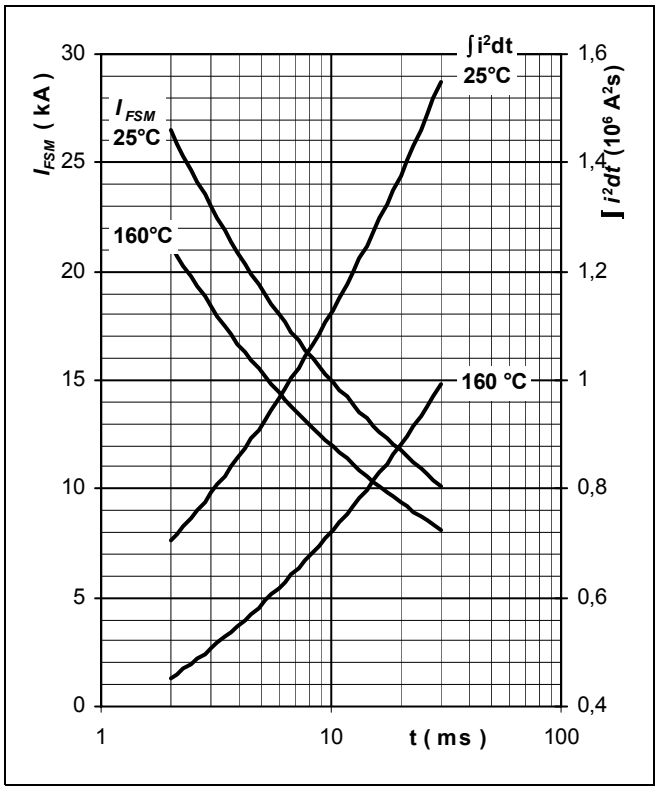

Fig. 3 Surge forward current vs. pulse length. Half sine wave, single pulse, V_R = 0 V

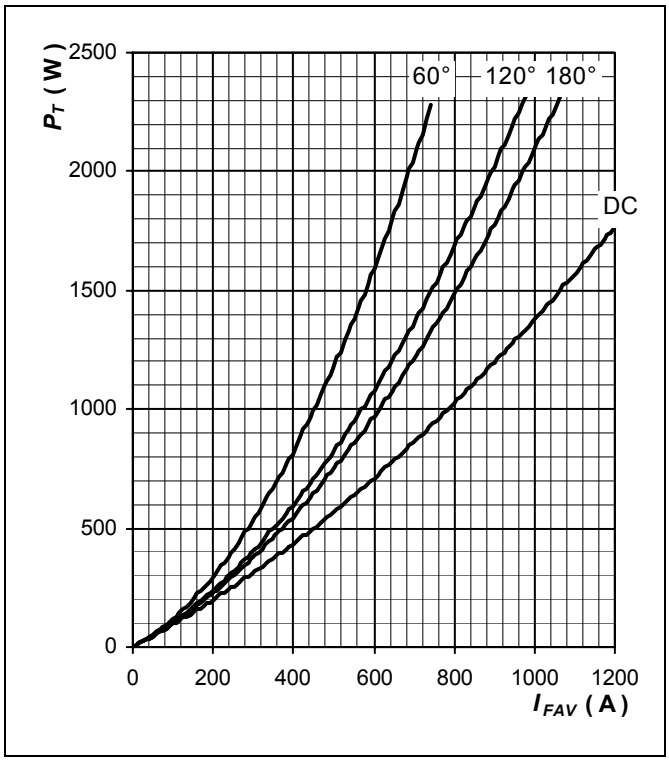

Fig. 4 Forward power loss vs. average forward current, sine waveform, f = 50 Hz

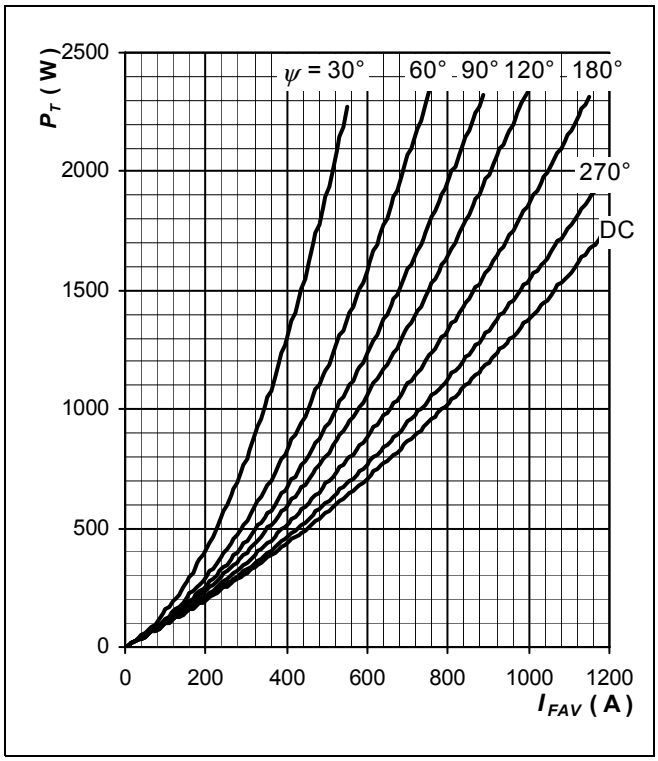

Fig. 5 Forward power loss vs. average forward current, square waveform, f = 50 Hz

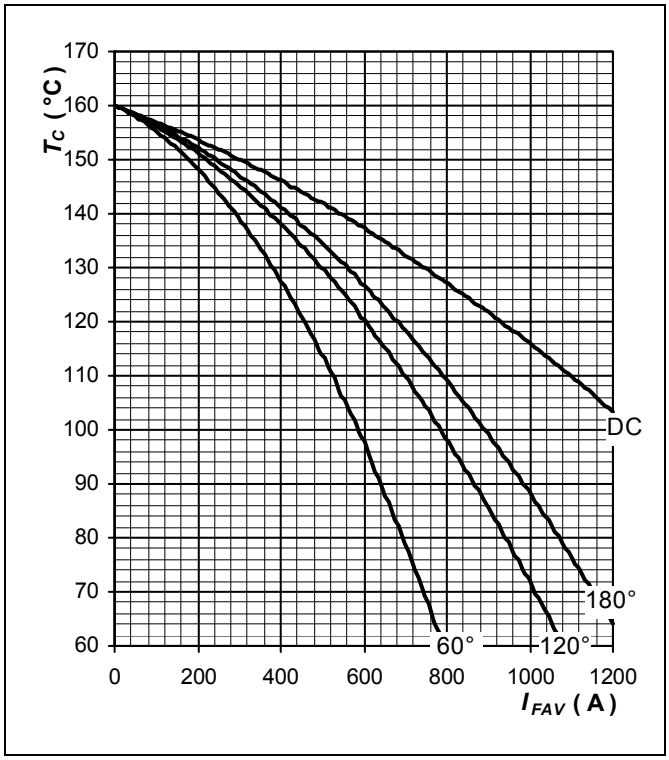

Fig. 6 Max. case temperature vs aver. forward current, sine waveform, f = 50 Hz

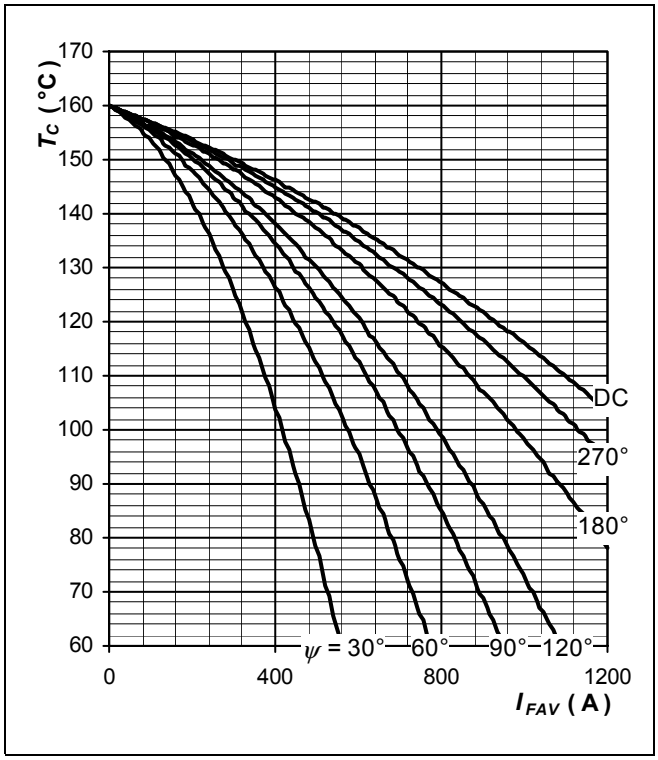

Fig. 7 Max. case temperature vs aver. forward current, square waveform, f = 50 Hz

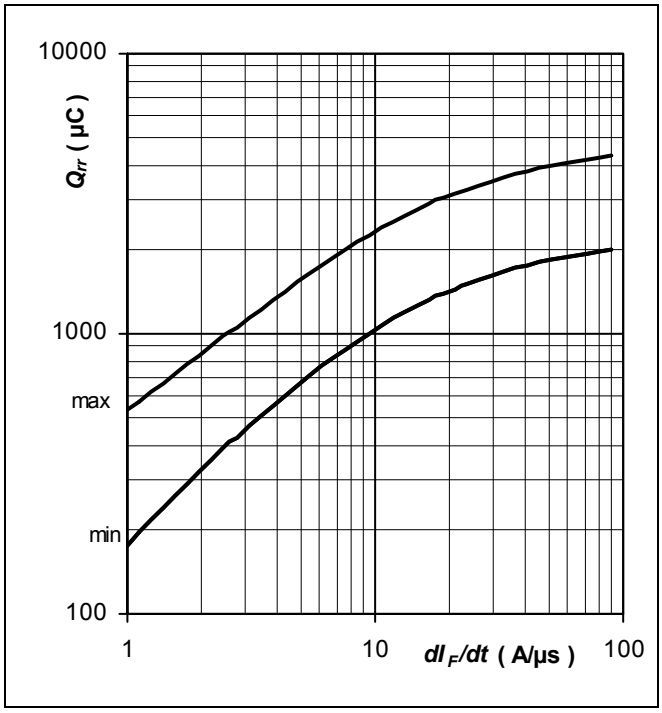

Fig. 8 Reverse recovery charge vs. dI_F/dt, I_F= 1000 A; $T_j = T_{jmax}$, limit values

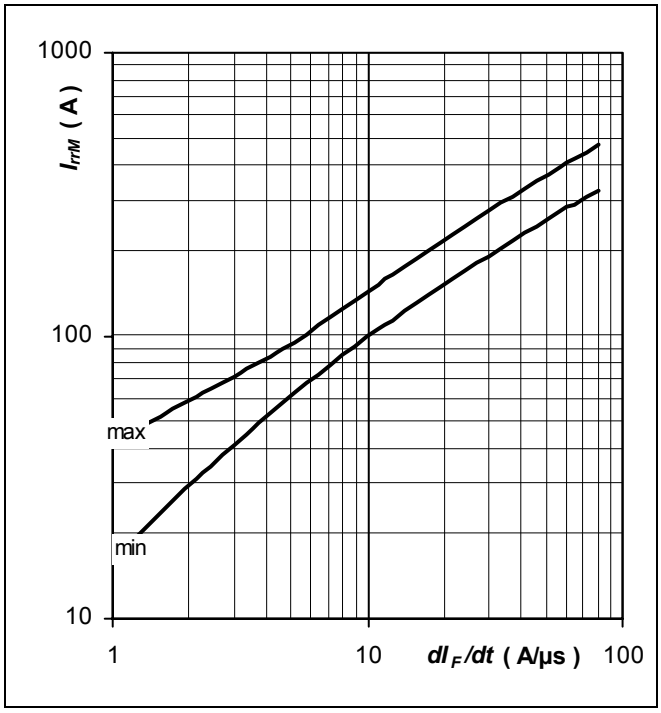

Fig. 9 Peak reverse recovery current vs. di_F/dt, I_F = 1000 A; $T_j = T_{jmax}$, limit values

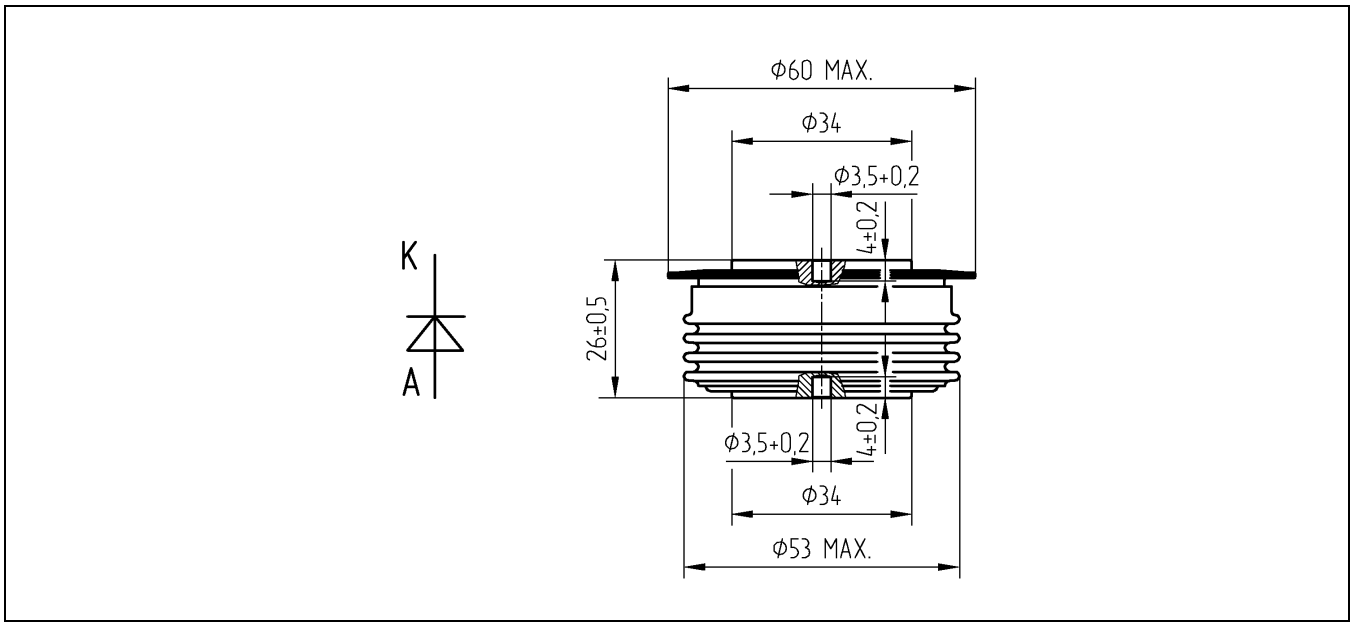

Fig. 10 Outline drawing. All dimensions are in millimeters and represent nominal values unless stated otherwise.

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